

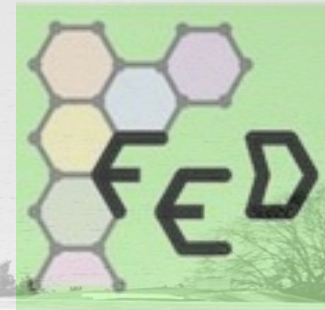
Layout Technique for Double-Gate Silicon Nanowire FET with an Efficient Sea-of-Tiles Architecture

Shashikanth Bobba

Prof. Giovanni De Micheli

March 25, 2013

Pierre-Emmanuel, Jian Zhang, Luca, Michele, Davide, Prof. Yusuf Leblebici



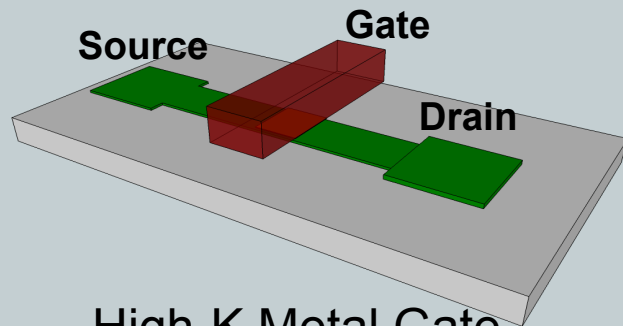
ÉCOLE POLYTECHNIQUE
FÉDÉRALE DE LAUSANNE

INTEGRATED SYSTEMS LABORATORY LSI

Functionally Enhanced Device

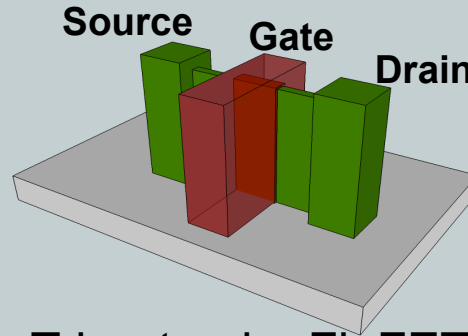
Miniaturisation: More Moore

32nm



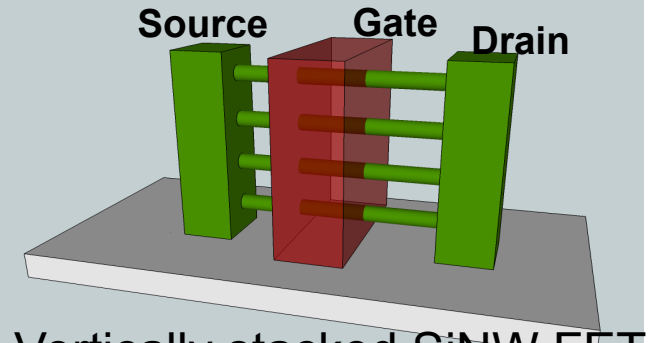
High-K Metal Gate

16nm

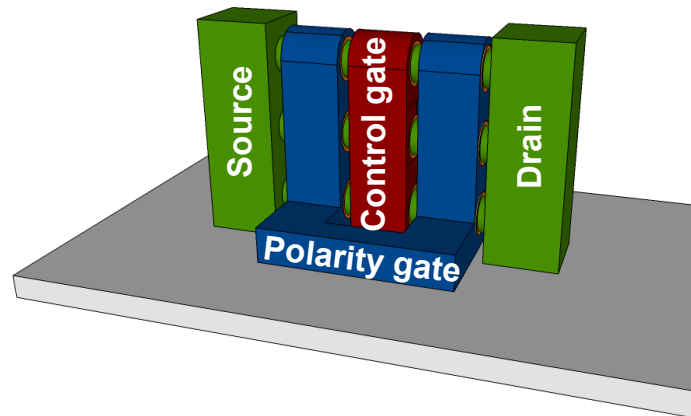


Tri-gate aka FinFET

10nm

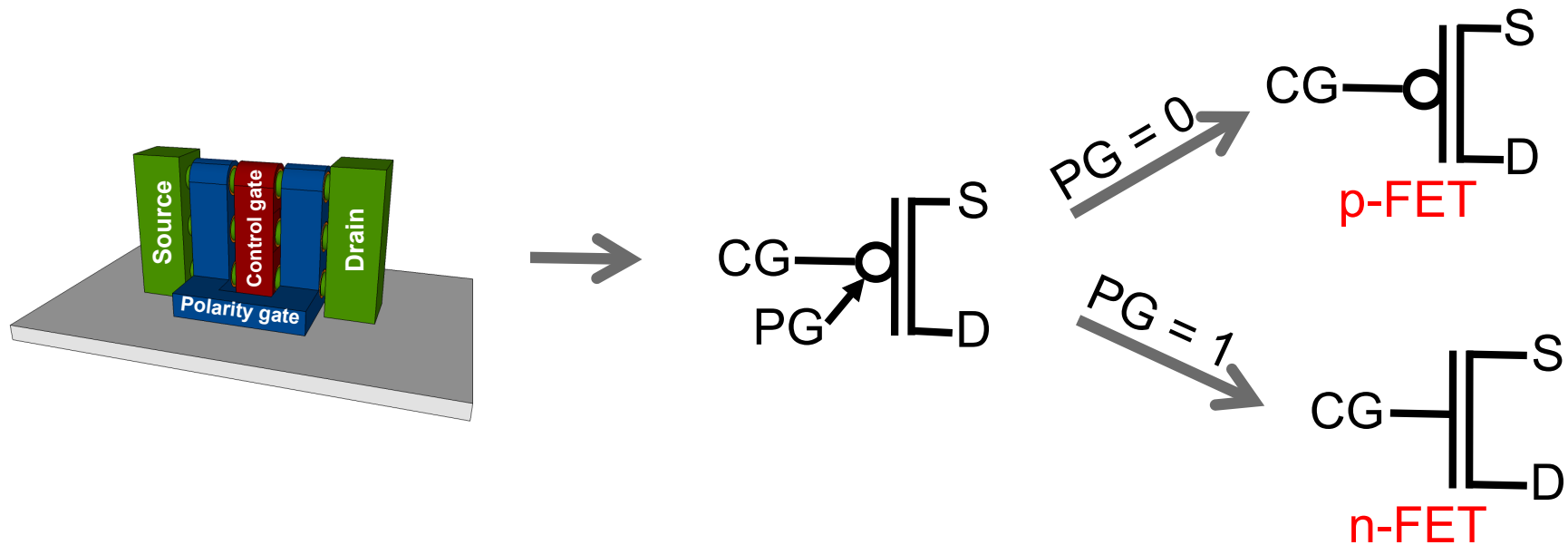


Vertically stacked SiNW FET



Enhanced
Functionality

Double-gate Silicon Nanowire FET

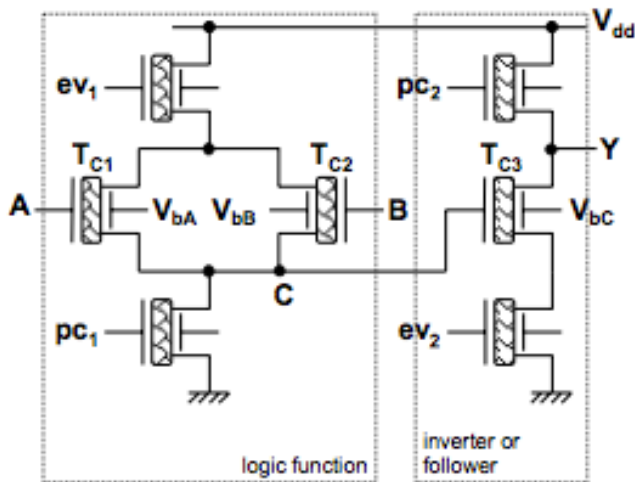


- Dynamic control on the polarity of the device
- Promising feature for future reconfigurable circuits
- Ambipolar logic circuits

Ambipolar Logic Circuits

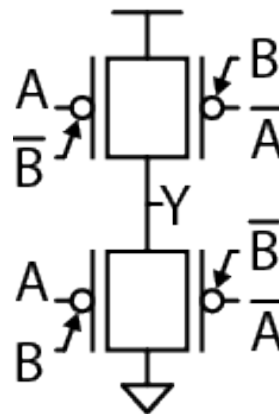
- Circuits based on double gate ambipolar transistors with controllable polarity (CNFET, SiNW FET, Graphene, ...)
- Optimal for XOR and XNOR dominated circuits

CNT-DR8F



O'Connor, ICECS 07

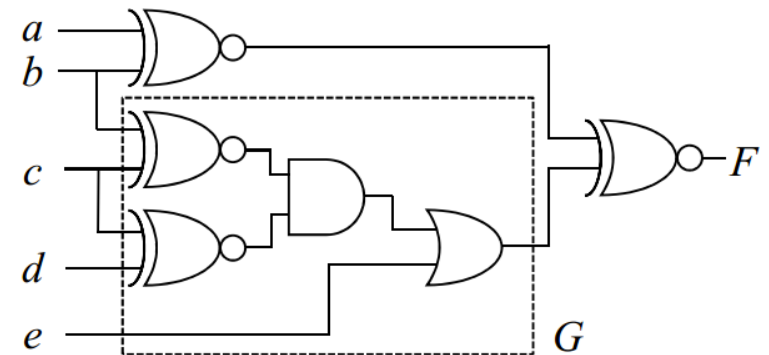
XOR2



Only 4 transistors

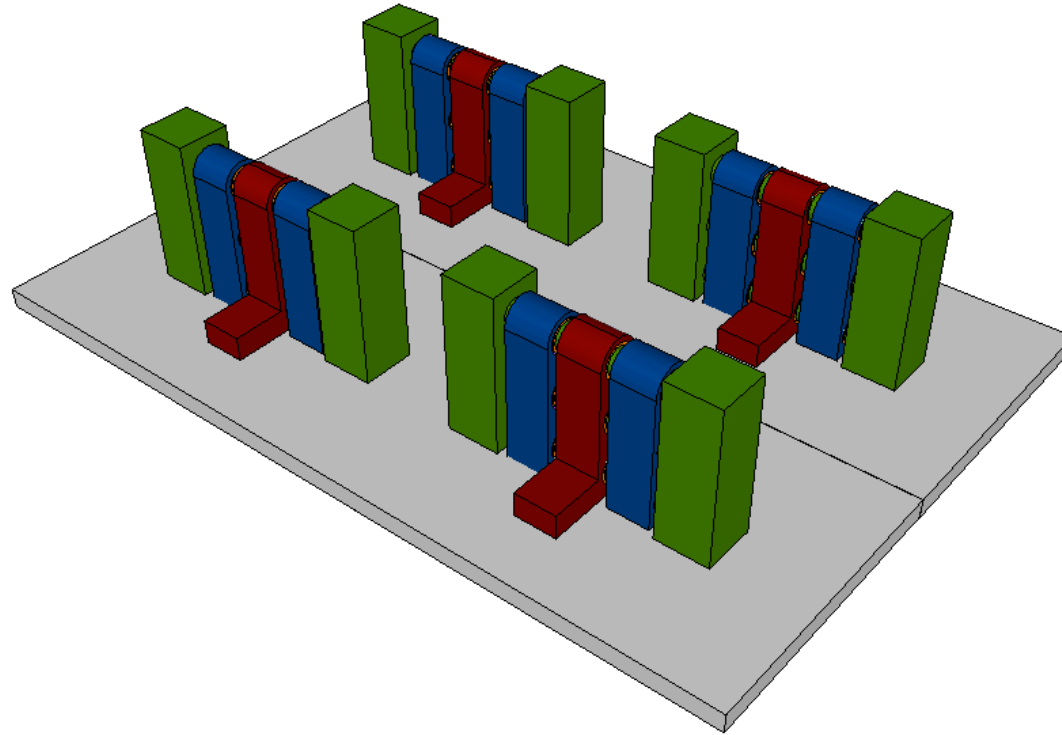
M-H. Ben Jamaa, PhD Thesis

ULM (5,3)



K. Mohanram, DAC 12

Motivation



XOR2 ??

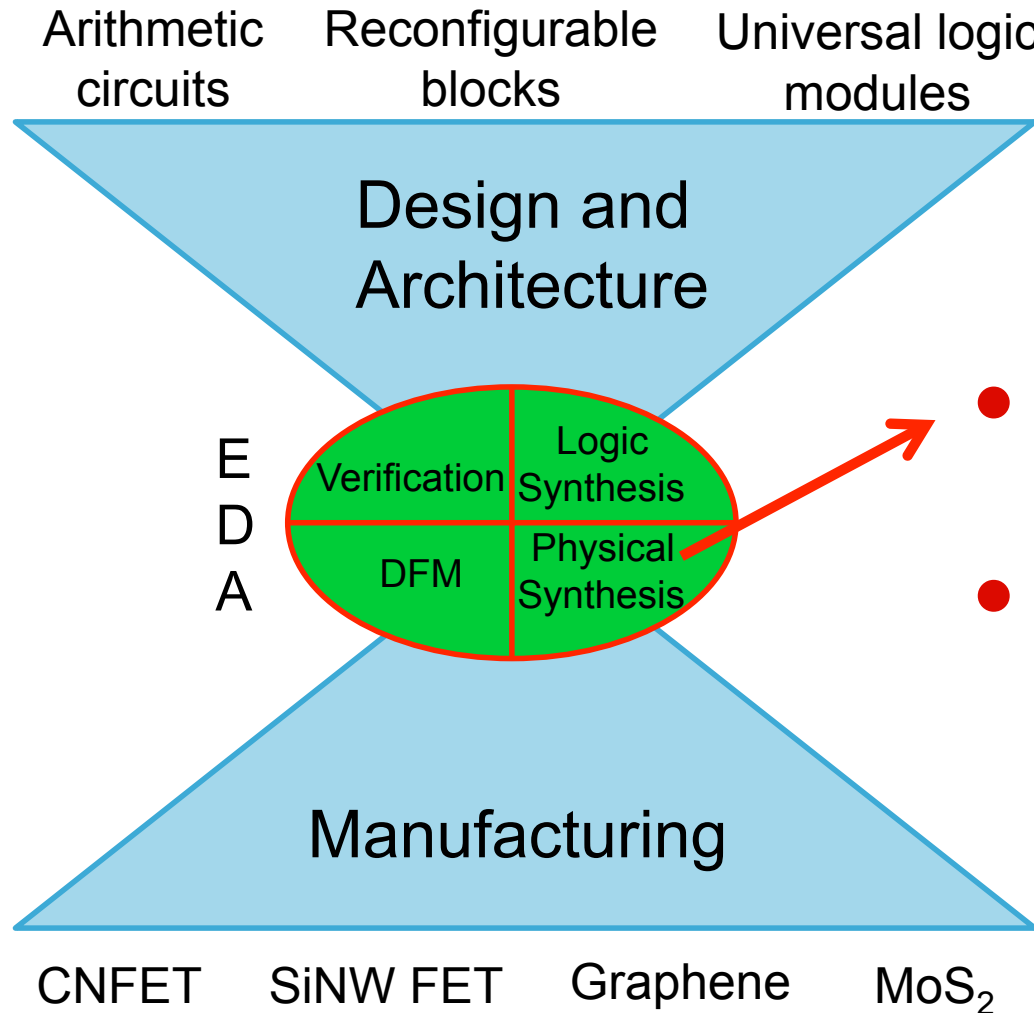


Fewer transistors for XOR operation



Every transistor has two gates to route

Physical Design Challenges



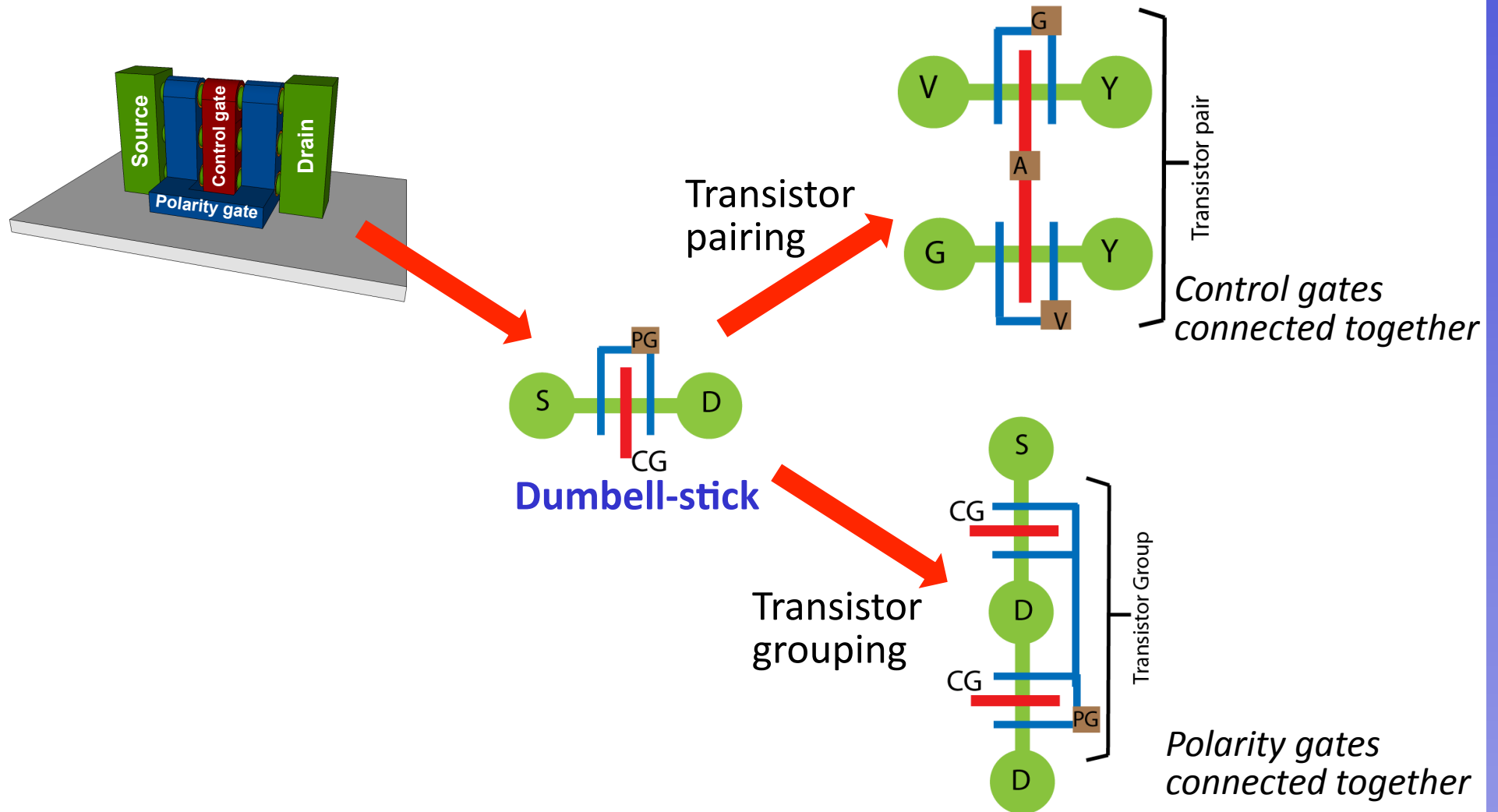
- Can we use existing layout techniques?
- Logic bricks for improved Yield

Outline

- Introduction
- Layout Technique for DG-SiNW FET
 - ⊙ Motivation
 - ⊙ Layout algorithm for XOR embedded Boolean functions
- Sea-of-Tiles
- Simulation Results
- Conclusion

Symbolic layouts : Dumbbell-stick diagrams

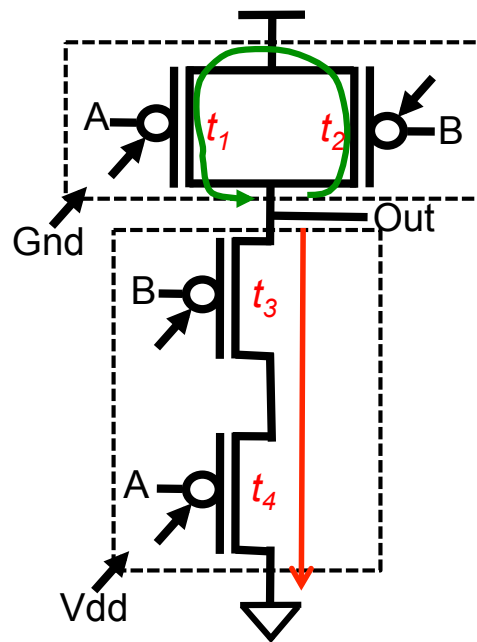
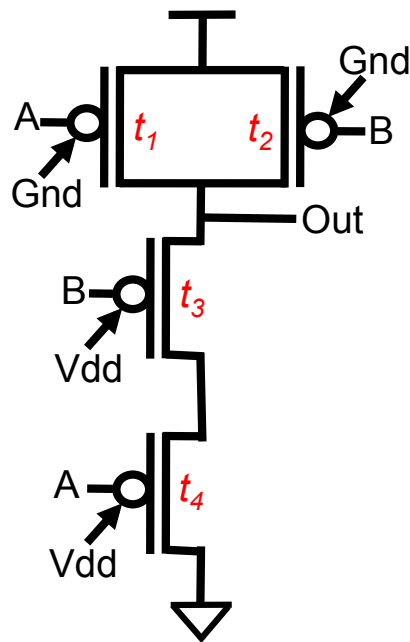
- Need for new symbolic layouts for ambipolar circuits



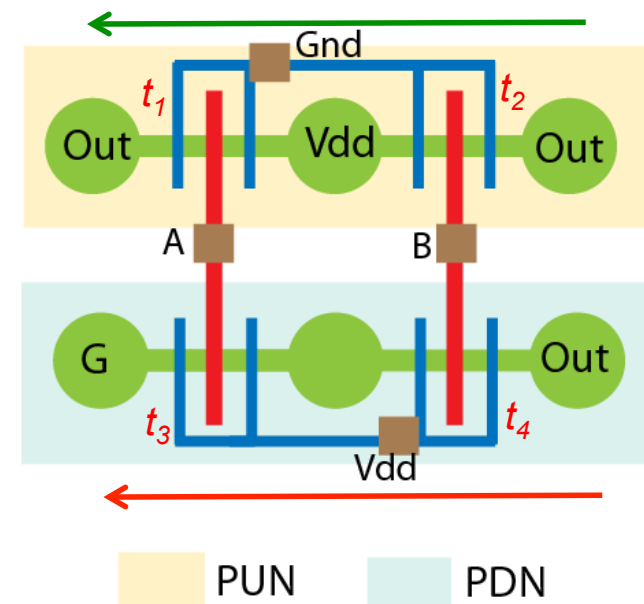
Layout technique for *Unate* logic functions

- Negative Unate functions: NAND, NOR, AOI, OAI
- Polarity gates are biased to either V_{dd} or Gnd

2-input NAND gate

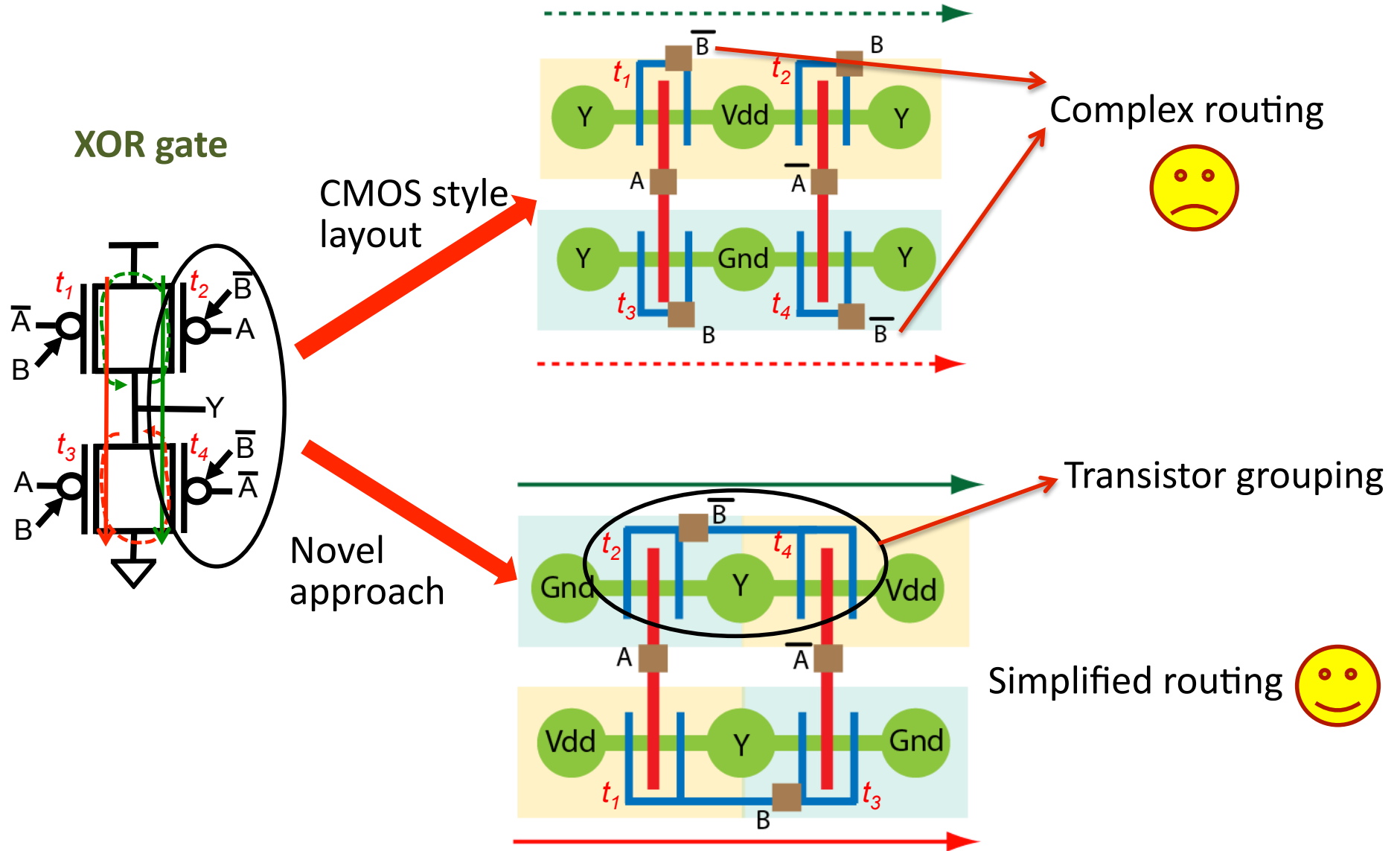


Only one polarity gate
for PUN and PDN



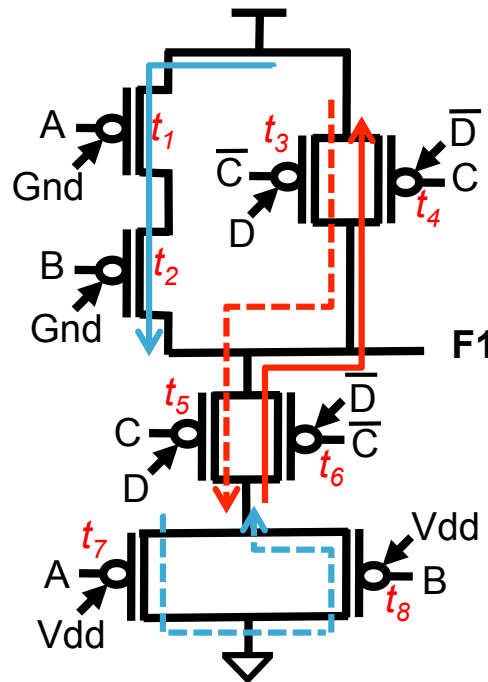
Dumbbell-stick
diagram

Layout technique for *Binate* logic functions



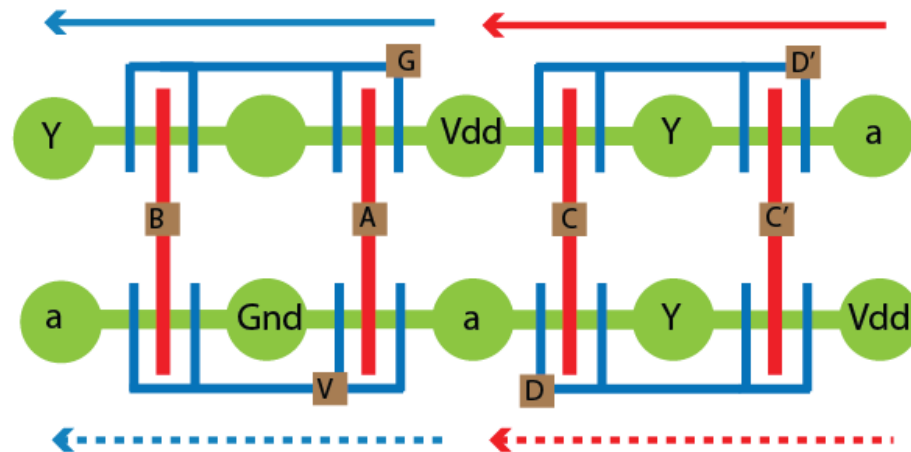
Complex gates with embedded XOR/XNOR

$$F1 = \overline{(A + B)(C \oplus D)}$$



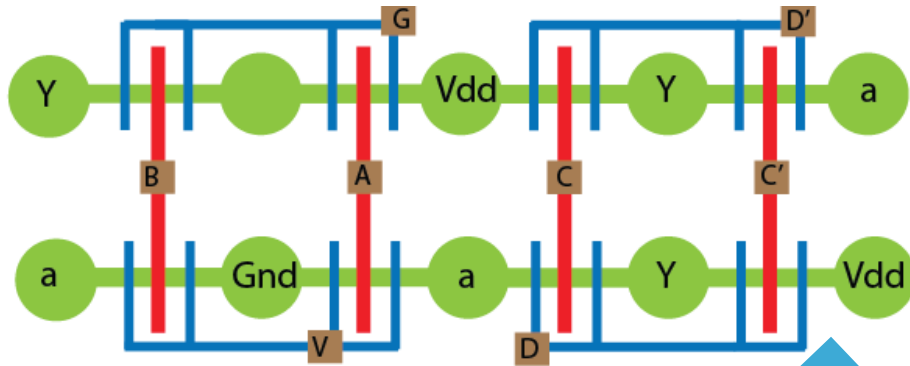
- ➔ a) Transistor grouping
- ➔ b) Transistor pairing
- ➔ c) Transistor ordering
- ➔ d) Transistor chaining

group D : { t_3, t_5 }
group \bar{D} : { t_4, t_6 }
group Vdd : { t_7, t_8 }
group Gnd : { t_1, t_2 }



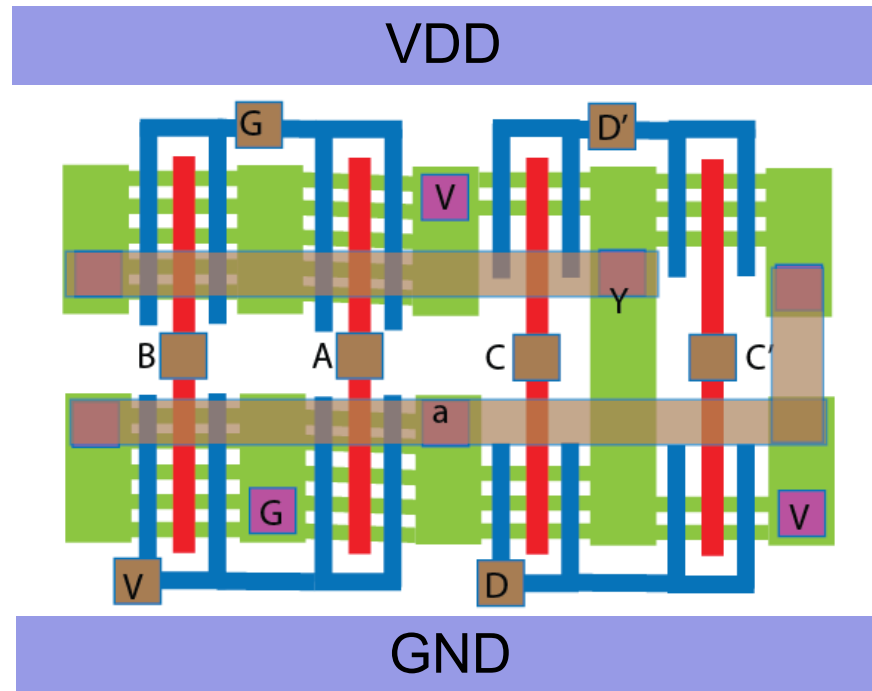
Dumbbell-stick diagram

Layout Extraction



Dumbbell-stick diagram

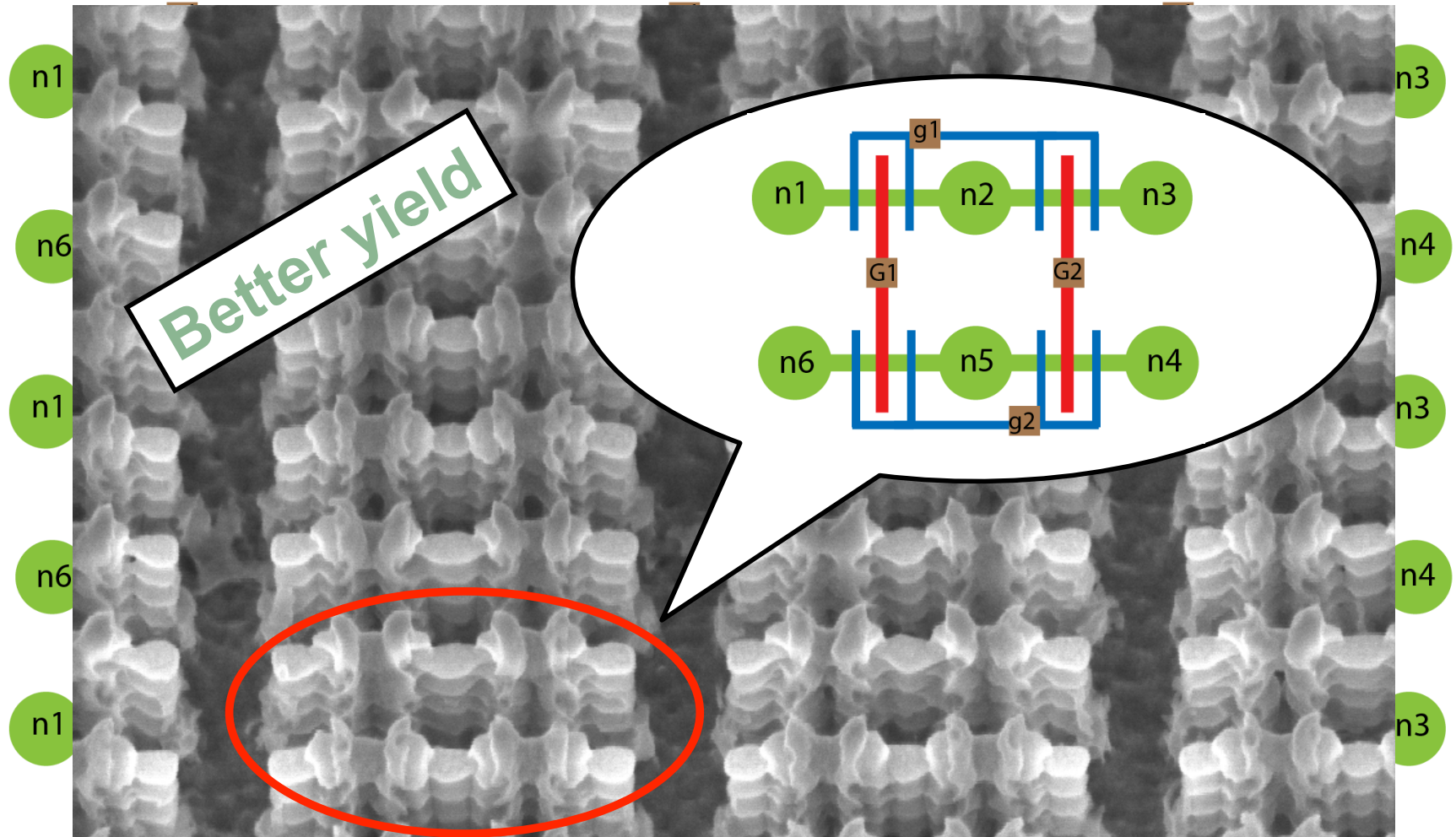
Transistor sizing + Layout generation



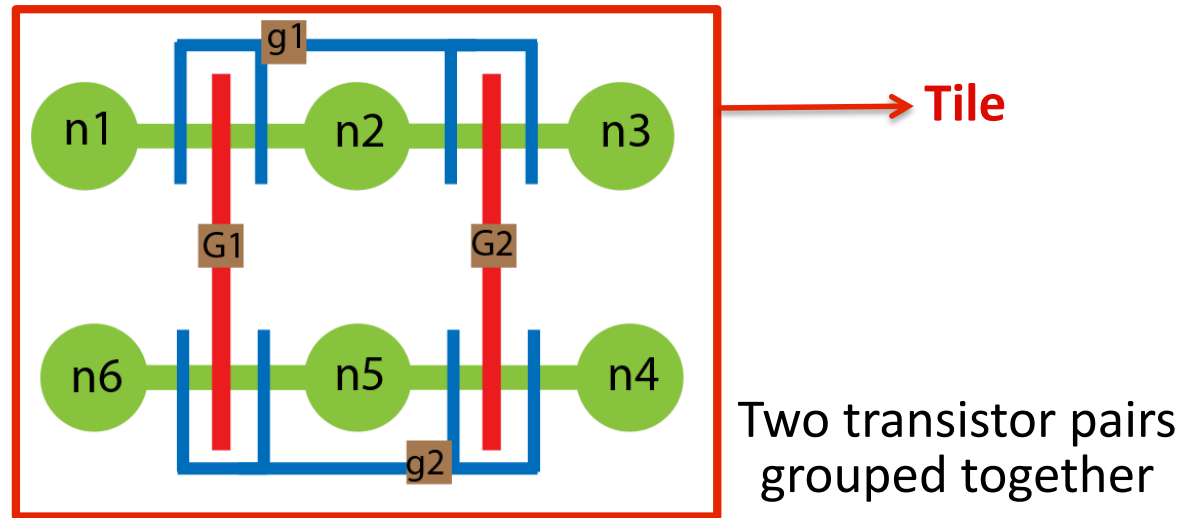
Outline

- Introduction
- Layout Technique for DG-SiNW FET
- Sea-of-Tiles
 - ⊙ Tiles as basic blocks
 - ⊙ Optimal Tile
 - ⊙ Power distribution for SoT
- Simulation Results
- Conclusion

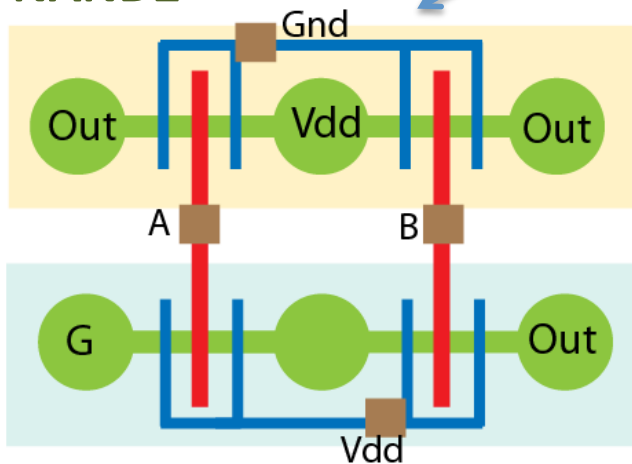
Sea-of-Tiles (SoT)



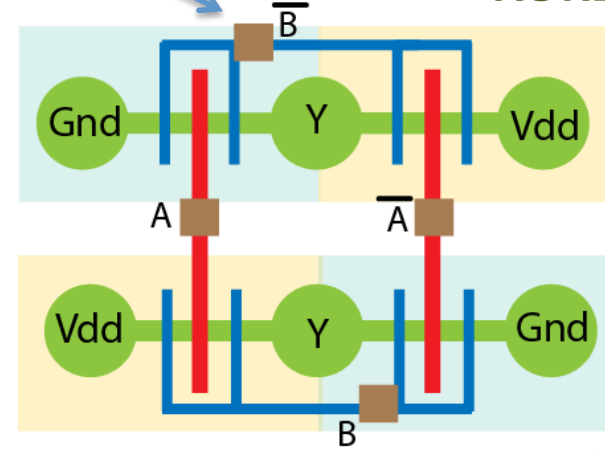
Layout regularity with *Tiles*



NAND2

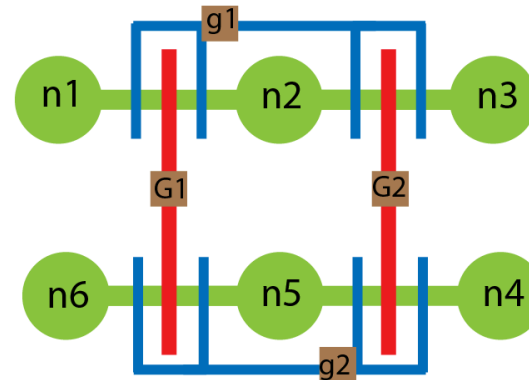


XOR2



Sea-of-Tiles (SoT)

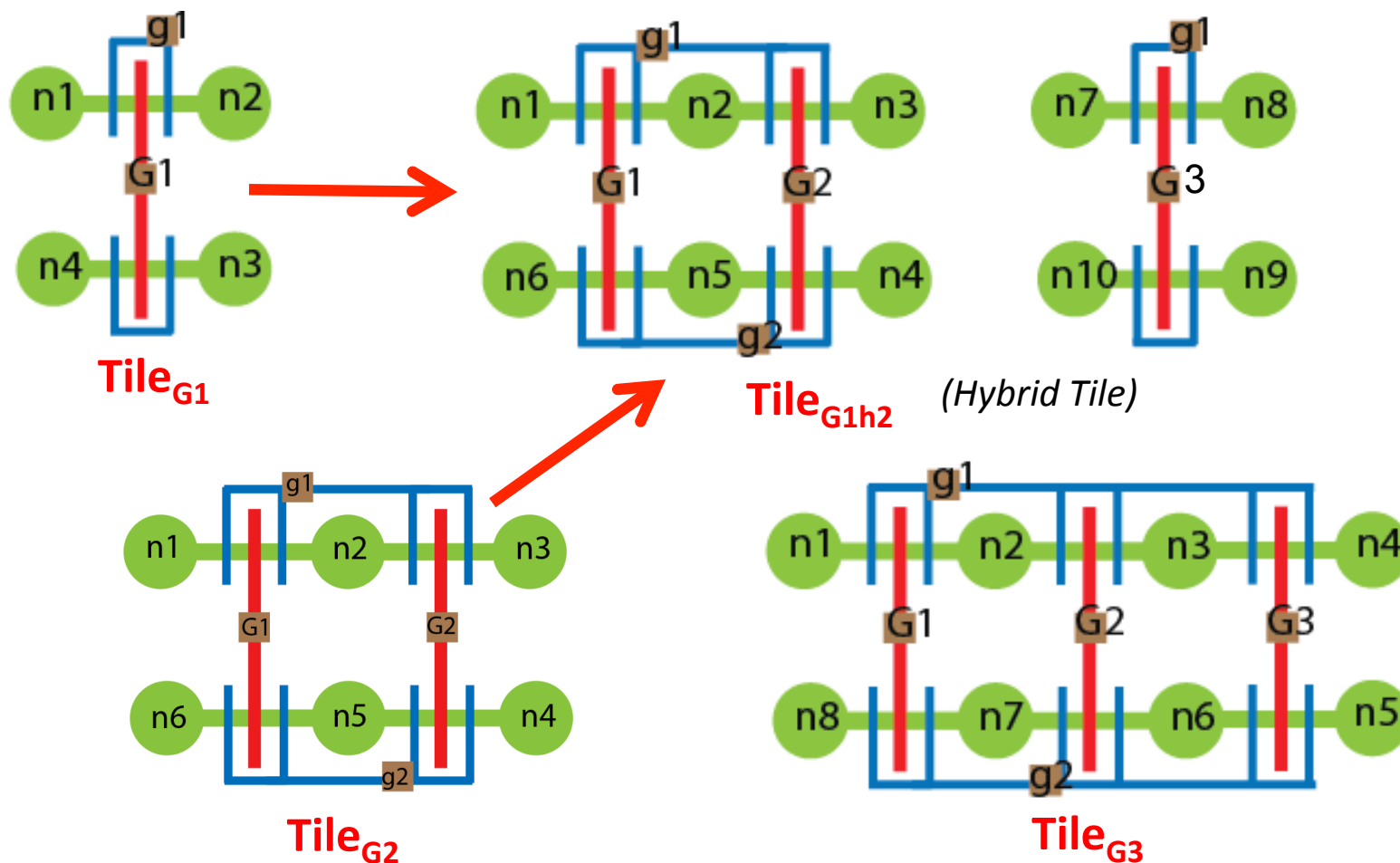
- Gate to Tile mapping



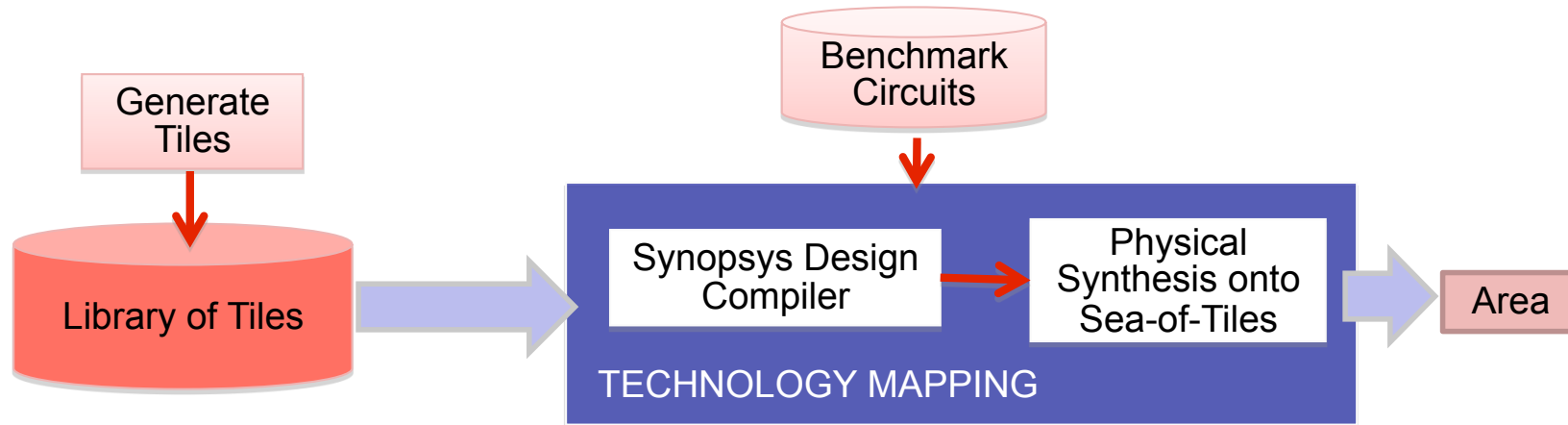
Gates	n1	n2	n3	n4	n5	n6	G1	G2	g1	g2
Xor2	Gnd	Out	Vdd	Gnd	Out	Vdd	A	A'	B'	B
Xnor2	Gnd	Out	Vdd	Gnd	Out	Vdd	A	A'	B	B'
Nand2	Out	Vdd	Out	Out	-	Gnd	A	B	Gnd	Vdd
Nor2	Vdd	-	Out	Out	Gnd	Out	A	B	Gnd	Vdd
Inv2X	Vdd	Out	Vdd	Gnd	Out	Gnd	A	A	Gnd	Vdd
Buf	O1	Vdd	O2	O2	Gnd	O1	A	O1	Gnd	Vdd

Various logic *Tiles* as basic building blocks

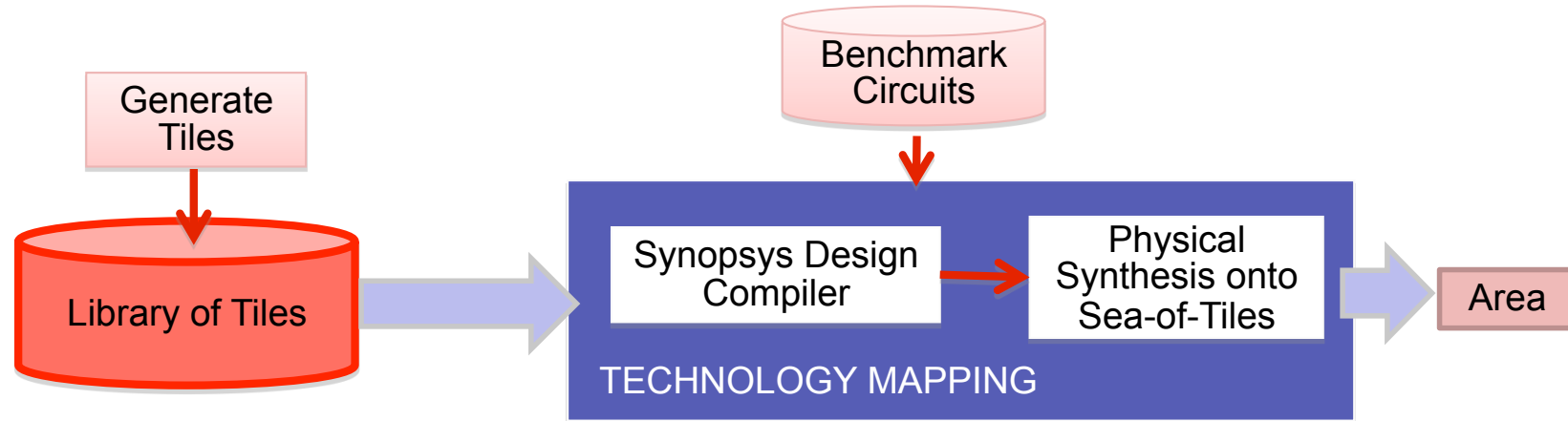
- What is the Optimal Tile?



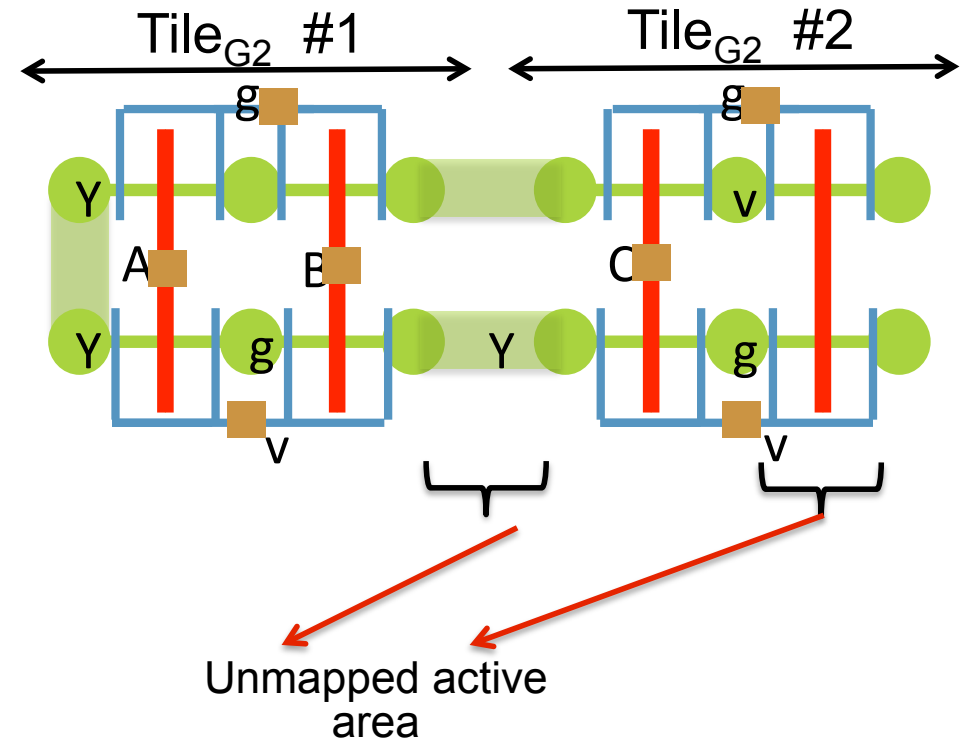
Design flow for determining the Optimal Tile



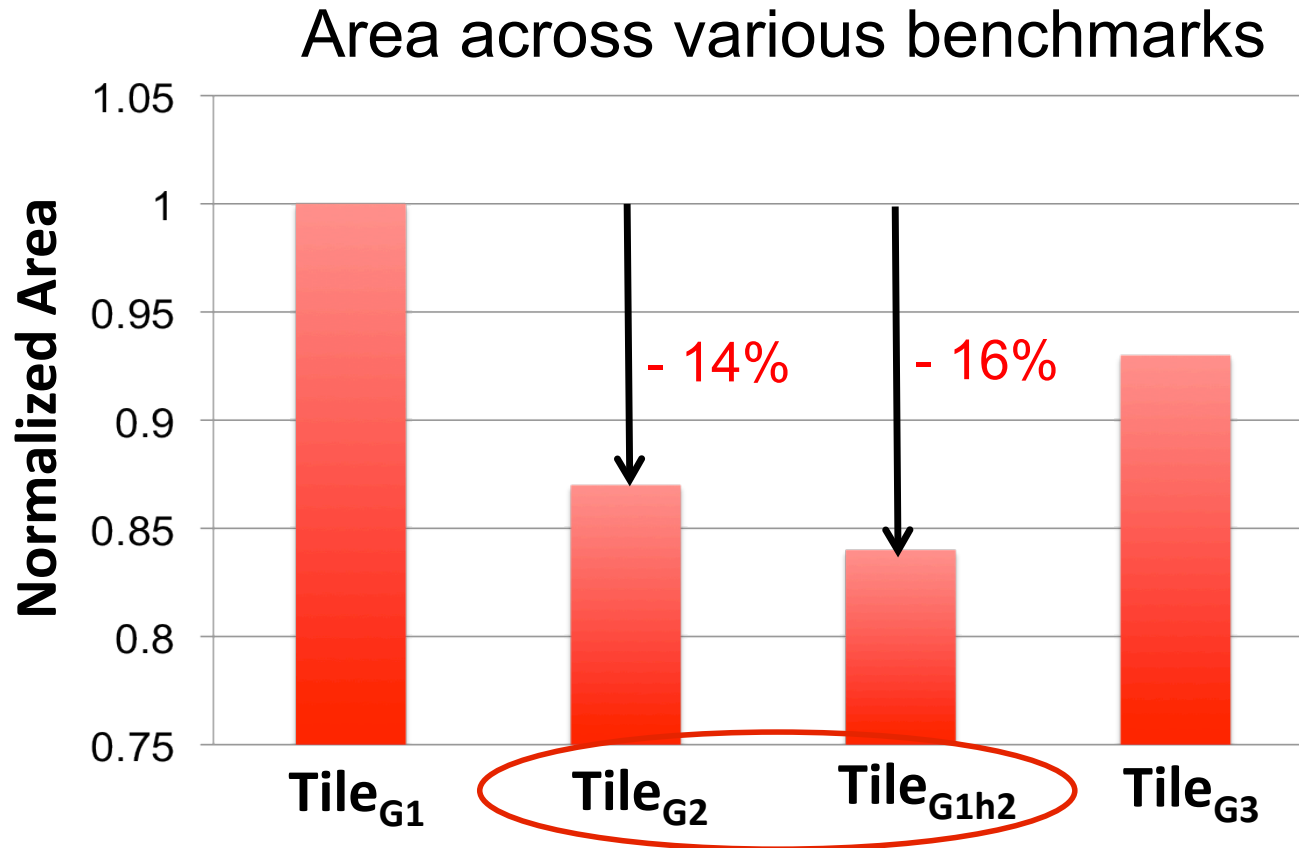
Design flow for determining the Optimal Tile



Gates	Tile _{G1}		Tile _{G2}		Tile _{G1h2}		Tile _{G3}	
	#N	#UF	#N	#UF	#N	#UF	#N	#UF
AND2	3	0.6	2	0.6	1	0.75	1	1
AND3	4	0.57	2	0.8	1.38	0.67	2	0.57
AOI21	3	0.6	2	0.6	1	0.75	1	1
AOI221	5	0.56	3	0.625	1.62	0.71	2	0.71
AOI222	6	0.54	3	0.75	2	0.67	2	0.86
AOI22	4	0.57	2	0.8	1.38	0.67	2	0.57
AOI321	6	0.54	3	0.75	2	0.67	2	0.86
BUF	2	0.66	1	1	0.62	1	1	0.67
INV	1	0.66	1	1	0.38	1	1	0.67
NAND2	2	0.66	1	1	0.62	1	1	0.67
NAND3	3	0.6	2	0.6	1	0.75	1	1
NAND4	4	0.57	2	0.8	1.38	0.67	2	0.57
NOR2	2	0.66	1	1	0.62	1	1	0.67
NOR3	3	0.6	2	0.6	1	0.75	1	1
NOR4	4	0.57	2	0.8	1.38	0.67	2	0.57
OAI21	3	0.6	2	0.6	1	0.75	1	1
OAI22	4	0.57	2	0.8	1.38	0.67	2	0.57
OR2	3	0.6	2	0.6	1	0.75	1	1
OR3	4	0.57	2	0.8	1.38	0.67	2	0.57
XNOR2	8	0.57	2	0.8	1.38	0.67	2	0.57
XNOR3	9	0.56	3	0.625	1.62	0.71	2	0.71
XOR2	8	0.57	2	0.8	1.38	0.67	2	0.57
XOR3	9	0.56	3	0.625	1.62	0.71	2	0.71

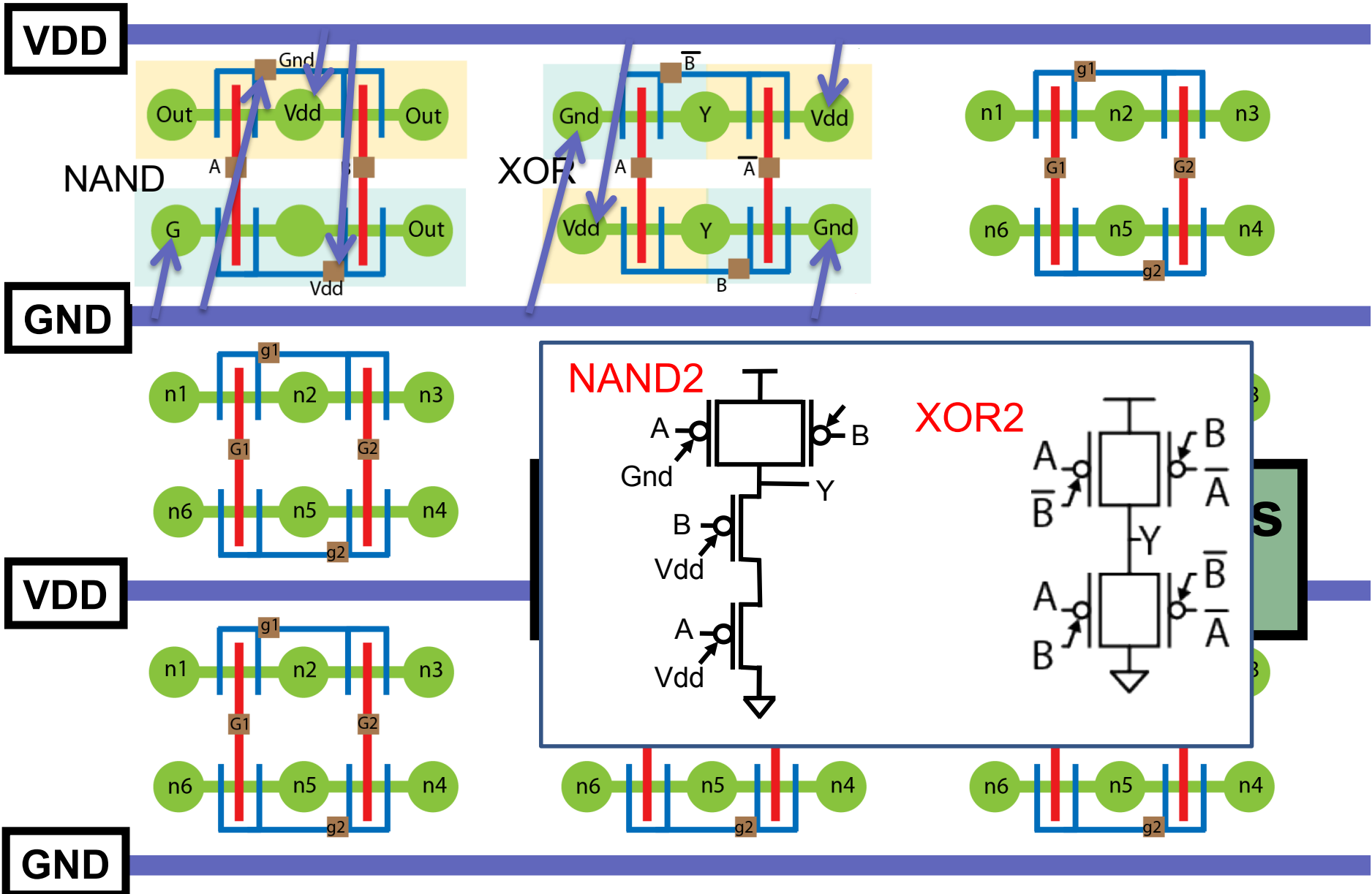


Result: Impact on Area



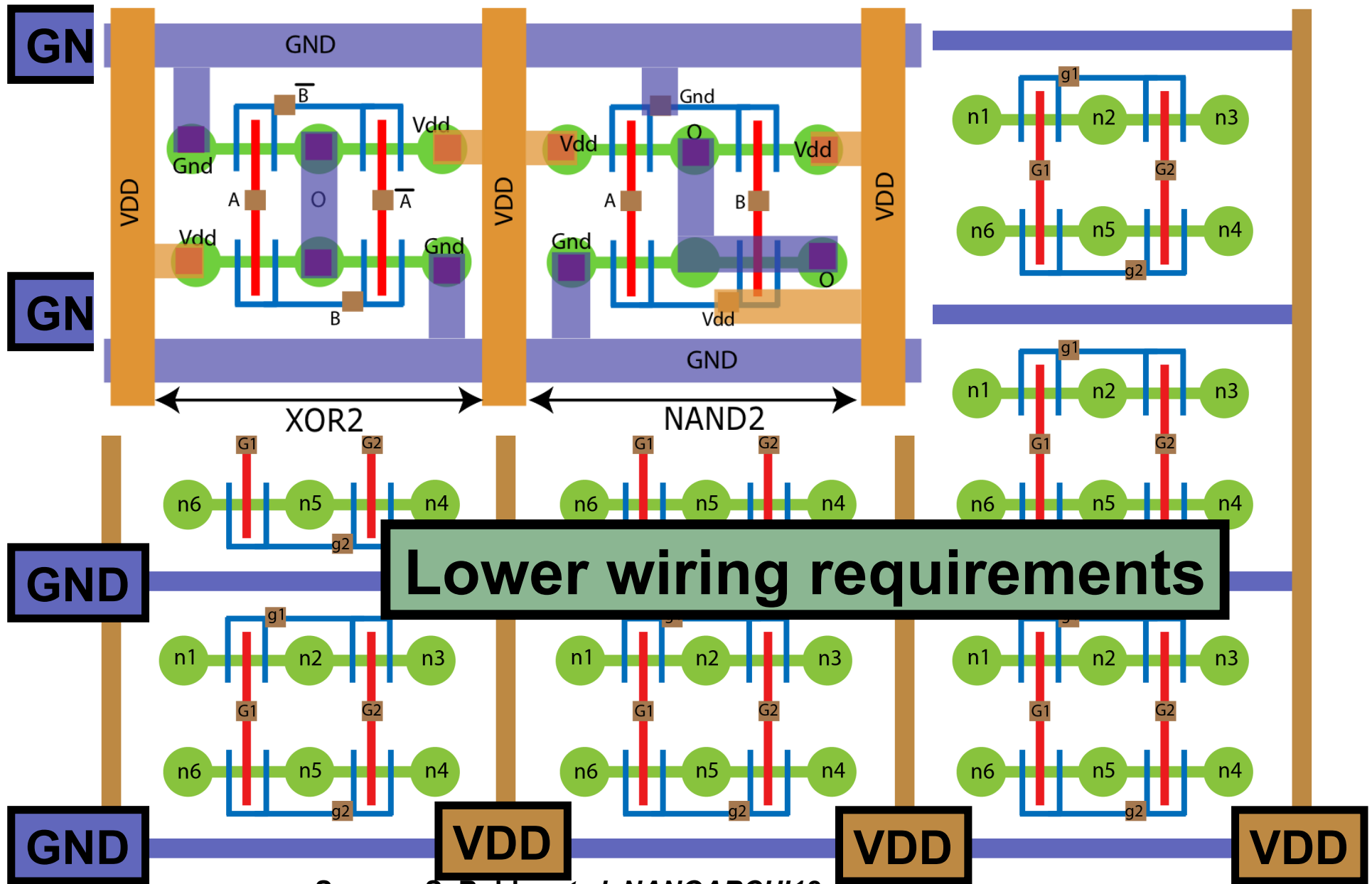
- Tile_{G2} and Tile_{G1h2} optimal for mapping logic gates, with respect to reduced routing complexity thereby reducing in the overall active area

Sea-of-Tiles Power Distribution...



Source: S. Bobba et al, NANOARCH'12

Sea-of-Tiles Power Distribution



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- Simulation Results
 - ⊙ Arithmetic Circuits
 - ⊙ Circuit level Benchmarking
- Conclusion

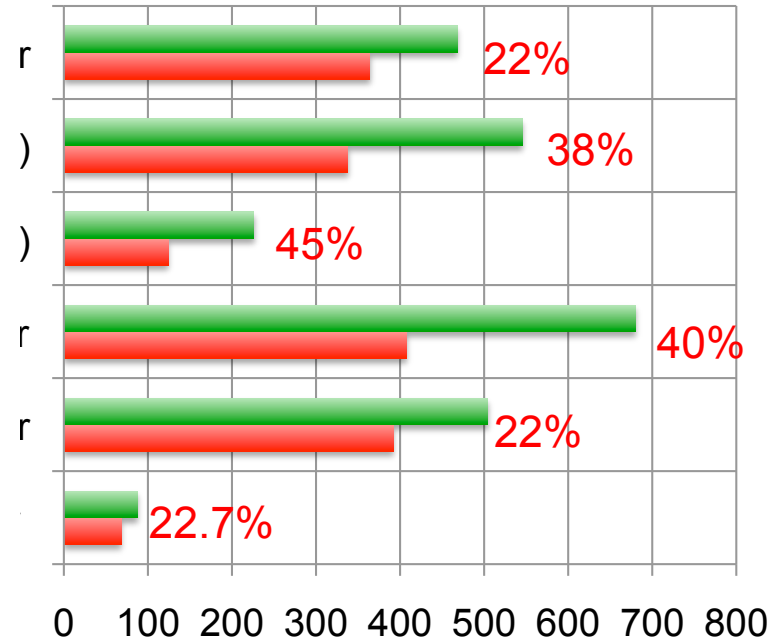
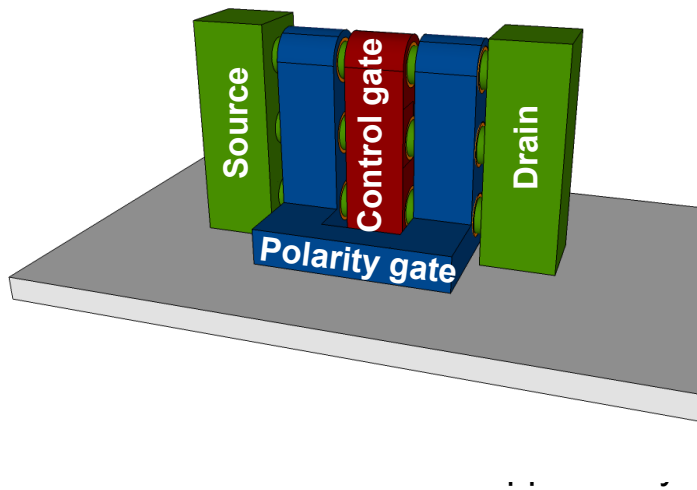
Case study: Arithmetic Circuits

Logic gates	FinFET (ns)	DG-SiNW (ns)		Si-CMOS (ns)
		CG -> Out	PG -> Out	
INV	0.056	0.043	X	0.139
NAND2	0.066	0.05	X	0.148
NOR2	0.062	0.072	X	0.172
XOR2	0.081	0.046	0.108	0.191
XOR3	0.198	0.079	0.11	0.38

Gate	Ambipolar Logic		CMOS logic	
	Area	Delay	Area	Delay
XOR2	8	1	12	1
XOR3	10	1.19	24	2
Half adder	12	1	16	1
Full adder	14	1.19	18	2
4-2 Compressor	26	2	42	4
5-3 Compressor	38	3	64	4

Logic Gates (FO4 delay)

Arithmetic Cell Library



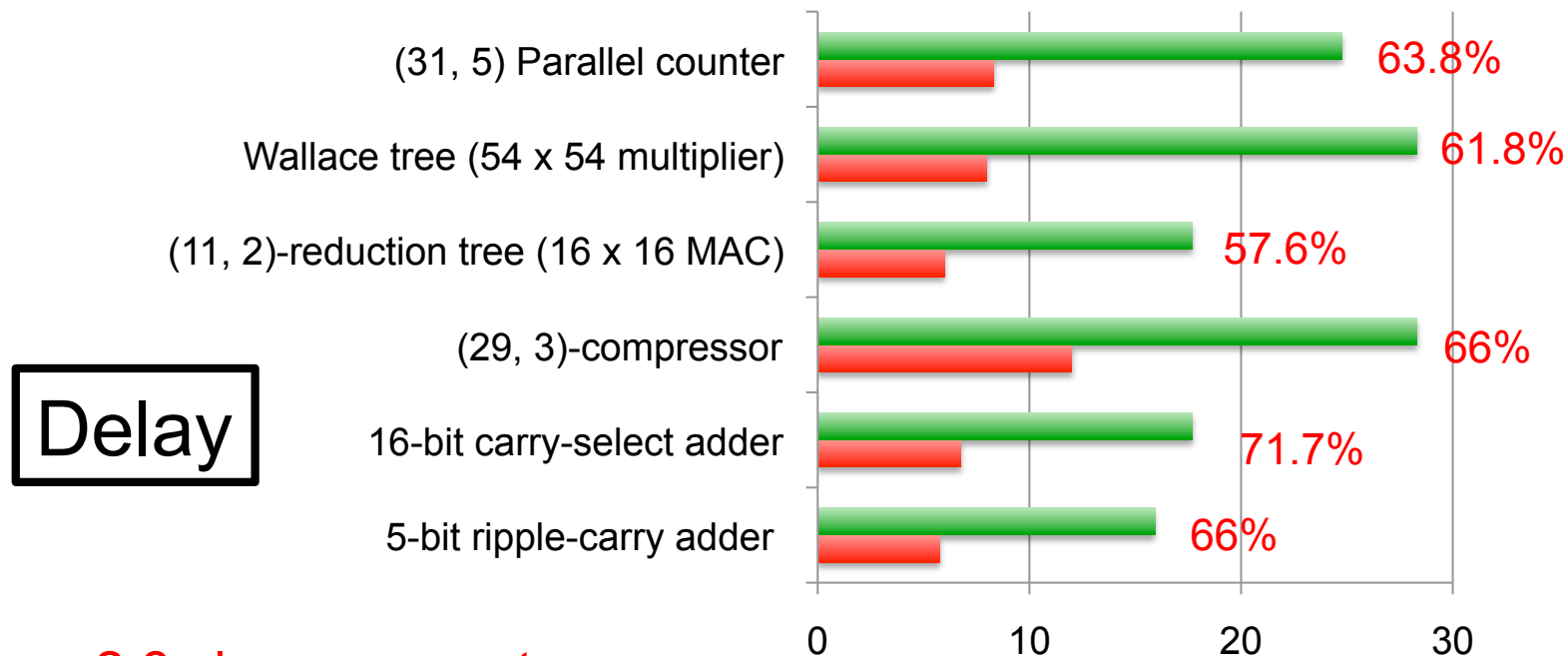
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Logic Gates

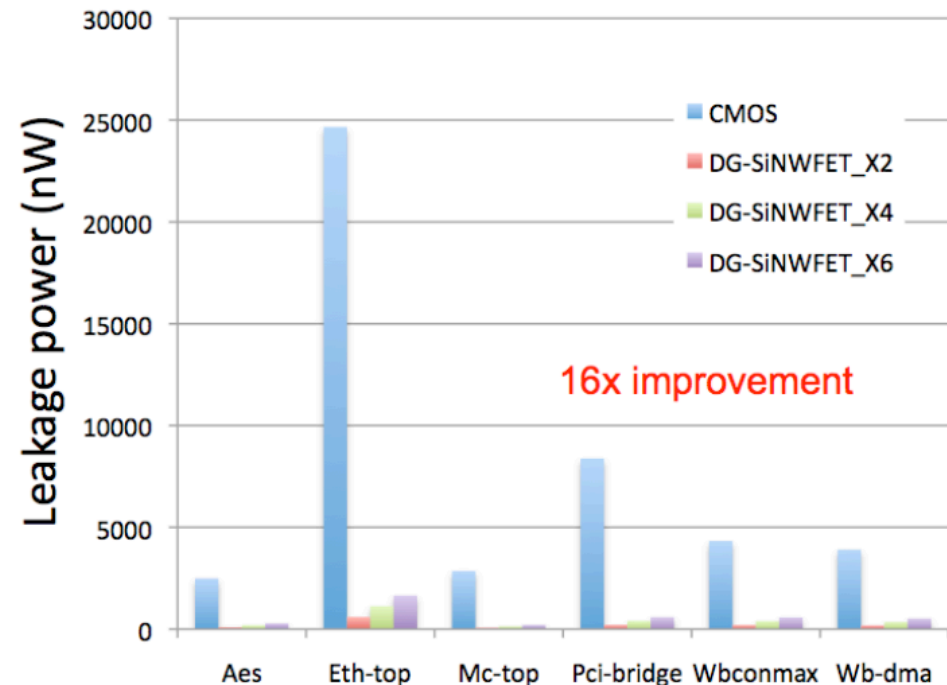
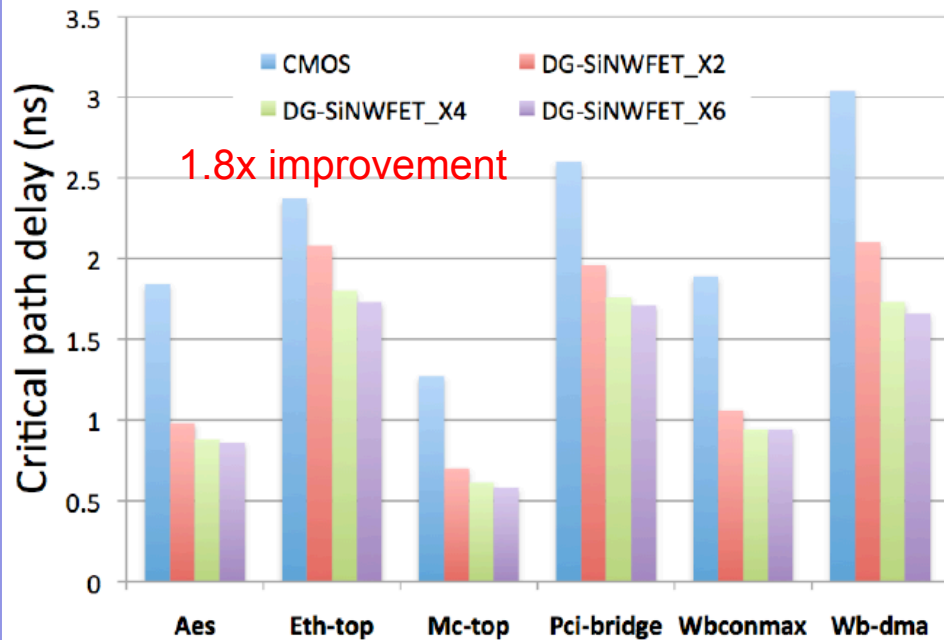
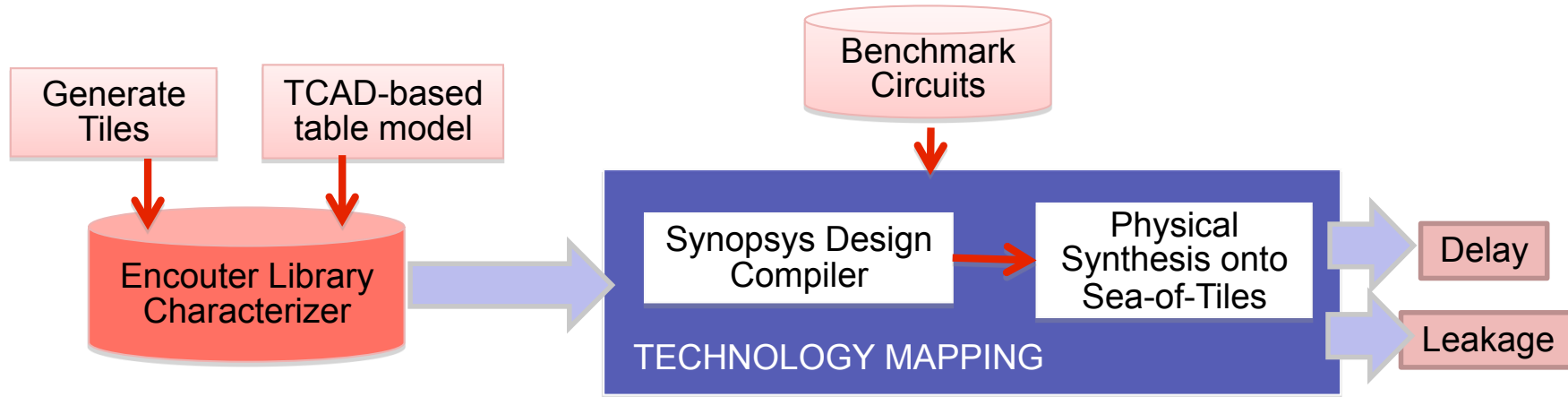
Arithmetic Cell Library



Delay

2.8x improvement

Circuit Level Benchmarking



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Conclusion

- Proposed a novel layout methodology and algorithm for Boolean functions with embedded XOR
- Showed an efficient implementation of Ambipolar circuits with Sea-of-Tiles design methodology
 - ❖ Area optimal tiles Tile_{G_2} and $\text{Tile}_{G_{1h2}}$
- Circuit Level Benchmarking
 - ❖ Maximum improvement for Arithmetic circuits (2.8x)
 - ❖ Reduction in Leakage power (16x)

Thank You